



# Model-Based MPC Enables Curvilinear ILT using Either VSB or Multi-Beam Mask Writers

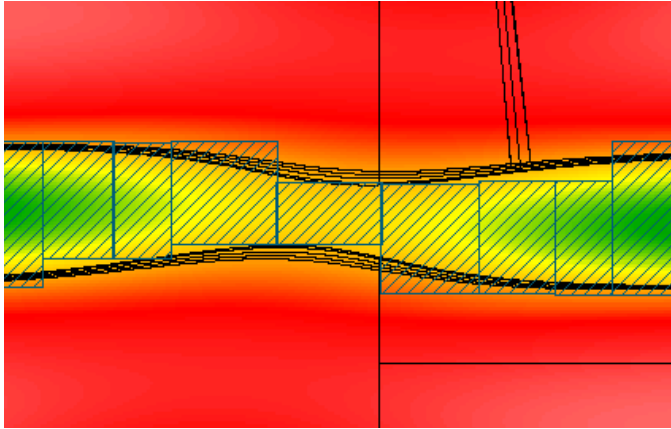
Leo (Linyong) Pang, Yutesu Takatsukasa, Daisuke Hara,  
Michael Pomerantsev, Bo Su, Aki Fujimura

D2S, Inc.

D2S Patented Technology

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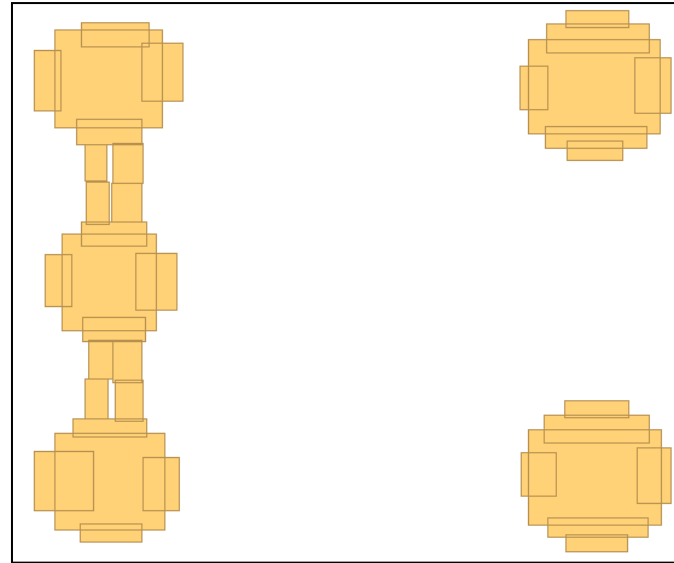
# GPU can Do Many Things in Semiconductor Manufacturing



## Litho Simulation

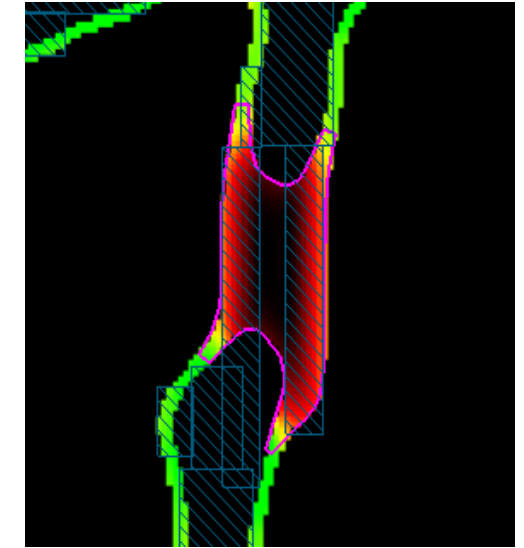
Wafer Plane Analysis (WPA) for Mask CD SEM (CSTIC paper)

High accuracy EPE measurement and Litho. Simulation capability for ILT, Kondo-san, Advantest



## Mask Data Prep

MDP with overlapping shots (This paper)



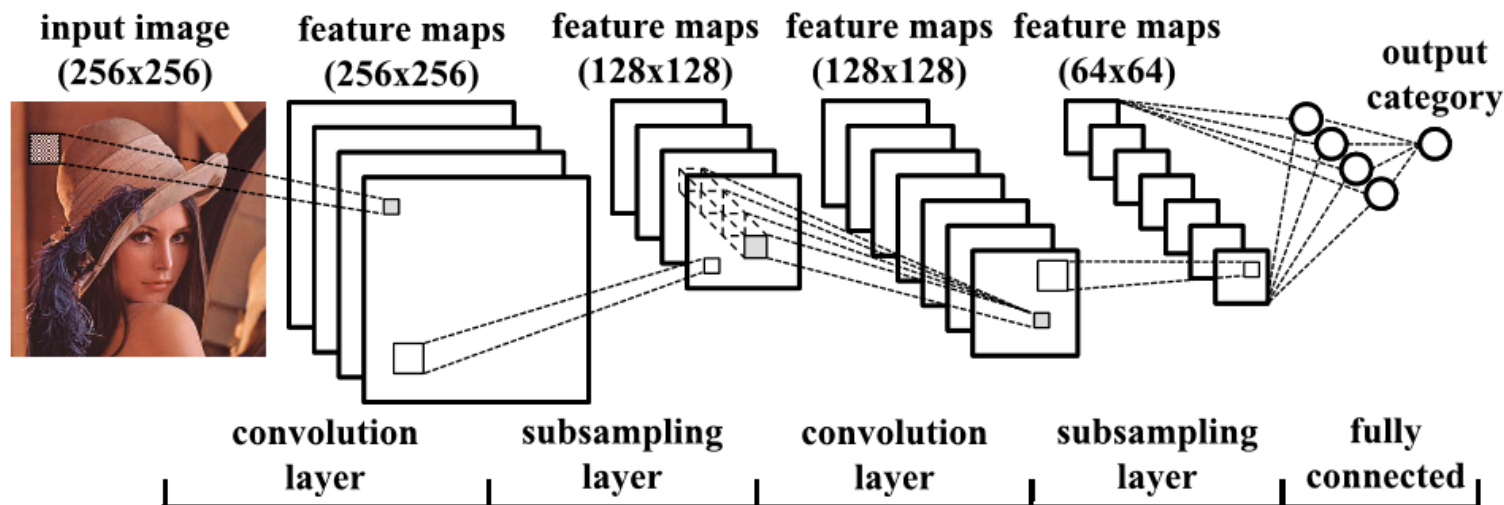
## Curvilinear Geometry Engine

EUV Modeling in the Multi-Beam mask making Era, Ryan Pearman

Simulation-Based MDP Verification for Leading-Edge Masks, Bo Su

# GPU can Do Many Things in Semiconductor Manufacturing <sup>D<sub>2</sub>S</sup>

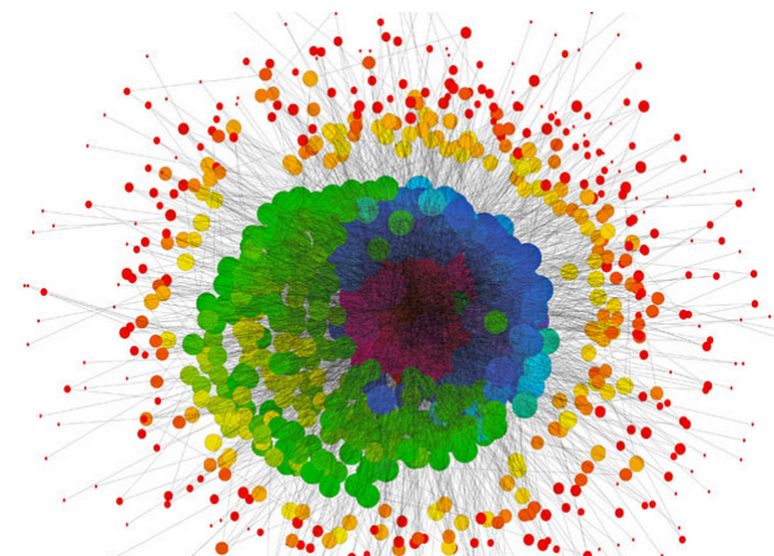
## Machine learning – GPU is the great platform



Deep learning with Convolutional Neural Network (CNN)

Ref: Minimizing Computation in Convolutional Neural Networks Jason Cong, Bingjun Xiao/CANN2014

Image and multi-dimensional data manipulation & computation



Ref: Multi-Dimensional Graph Data Opens the Door to New Applications, David S. Frankel

- Electron Beam Lithographic Modeling Assisted by Artificial Intelligence Technology, Nakayamada-san, NuFlare
- Data Analytics and Machine Learning for Design-Process-Yield Optimization in Electronic Design Automation and IC Semiconductor Manufacturing, Luigi Capodieci, Motivo
- Accurate Lithography Simulation Model based on Convolutional Neural Networks, Yuki Watanabe, Toshiba
- Imbalance Aware Lithography Hotspot Detection: A Deep Learning Approach, H. Yang, Chinese University of Hong Kong /Brion (SPIE)

# A Decade of ILT!

## Fast Inverse Lithography Technology

Daniel S. Abrams, Linyong Pang  
Luminescent Technologies, Inc., 650 Castro Street, Suite 220, Mountain View, CA 94041, U.S.A.

Email: [leo@luminescent.com](mailto:leo@luminescent.com)



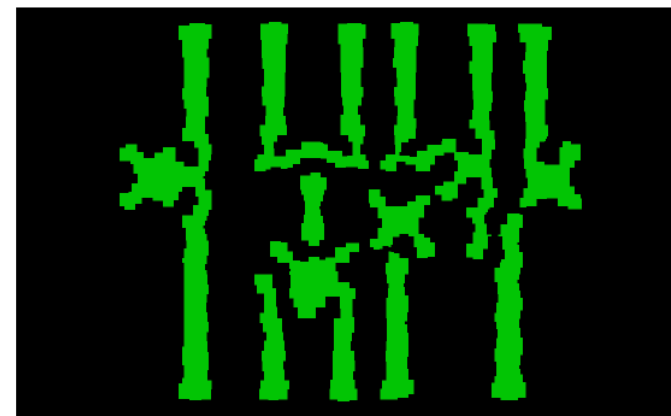
6

Papers



2

Foundries



1

Memory

1

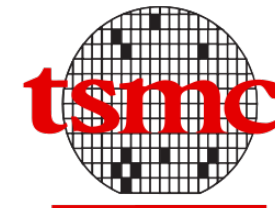
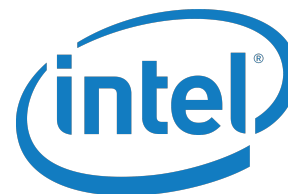
Mask shop





# ILT Adopted as the Way Forward

>200  
Papers



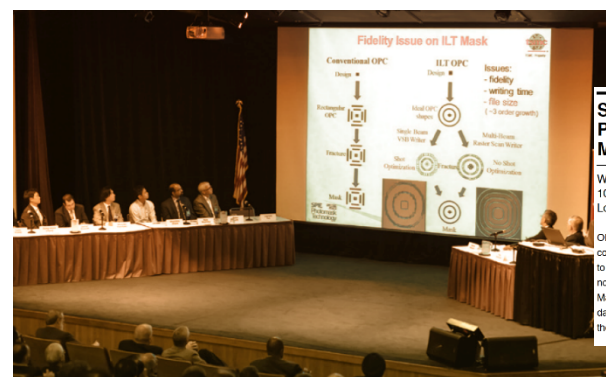
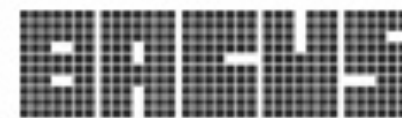
台灣積體電路製造股份有限公司  
Taiwan Semiconductor Manufacturing Company, Ltd.

Officially  
announced

# Today



台灣積體電路製造股份有限公司  
Taiwan Semiconductor Manufacturing Company, Ltd.



Session PNL:  
Panel Discussion: The Impact of Full-scale Curvilinear ILT OPC on Photomask  
Manufacturing

Wednesday 14 September 2016  
10:30 AM - 12:30 PM  
Location: Conv. Ctr. Room LL20

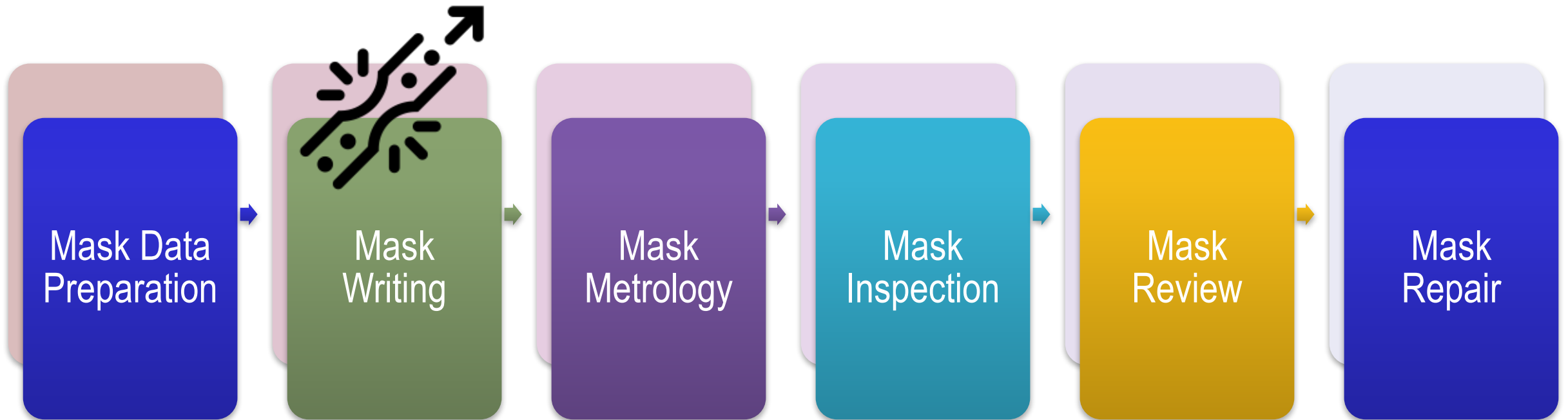
OPC performed with Inverse Lithography Technology (ILT) is used today primarily as a local repair process for OPC hotspot regions. ILT OPC is generally considered to be too computationally expensive to use on full layouts. Due to write time limitations, the raw curvilinear OPC output is typically "Manhattanized" to make masks manufacturable, primarily since the VSB mask writers used today are optimized for Manhattan data and slow down considerably when writing non-orthogonal figures. However, the computational cost of full-layout ILT OPC relative to its perceived value is lowering. In addition there is concern that the Manhattanization process reduces OPC accuracy. The introduction of multi-beam raster mask writers is expected to reduce the write time cost of raw ILT mask data compared to VSB writers, possibly soon making full-layout ILT OPC a reality. It is expected that the new raster writers level the playing field – both reducing the write time for ILT, but also removing the write time advantage of simpler mask patterns. Is the mask industry ready for the complexity of full-layout raw ILT?

ILT expertise proliferated

2014 panel

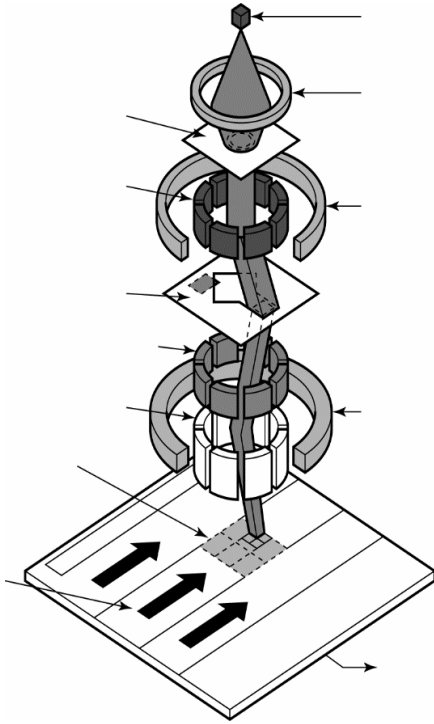
2016 panel

# Mask Writing Used to be the Bottleneck for Curvilinear ILT Masks in Mask Making

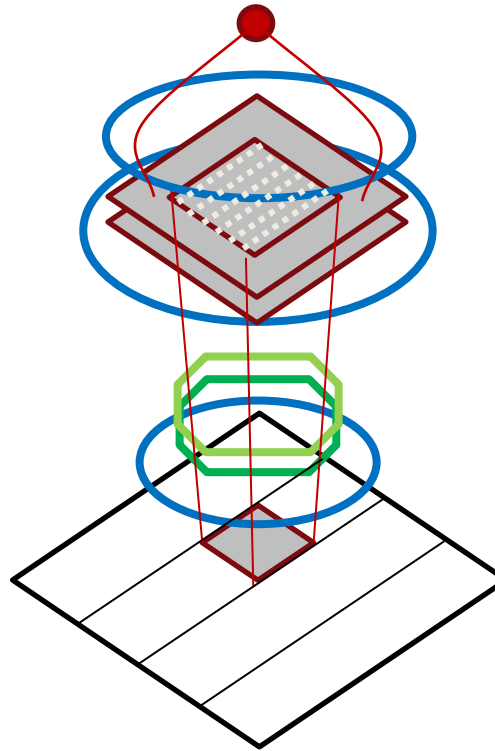


# VSB Mask Writer was Designed for Manhattan Patterns

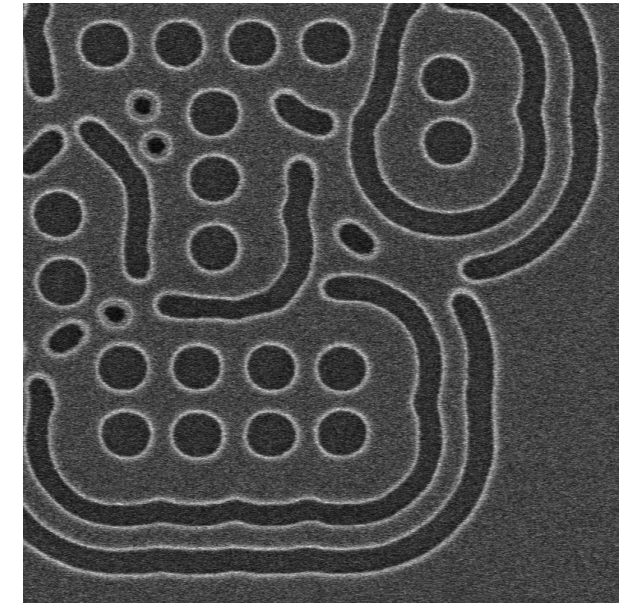
## Multi-beam is Designed for Curvilinear ILT Patterns



Variable shaped Beam  
Single beam, rectangular shape



Multi-beam Mask Writing  
Massive pixel array



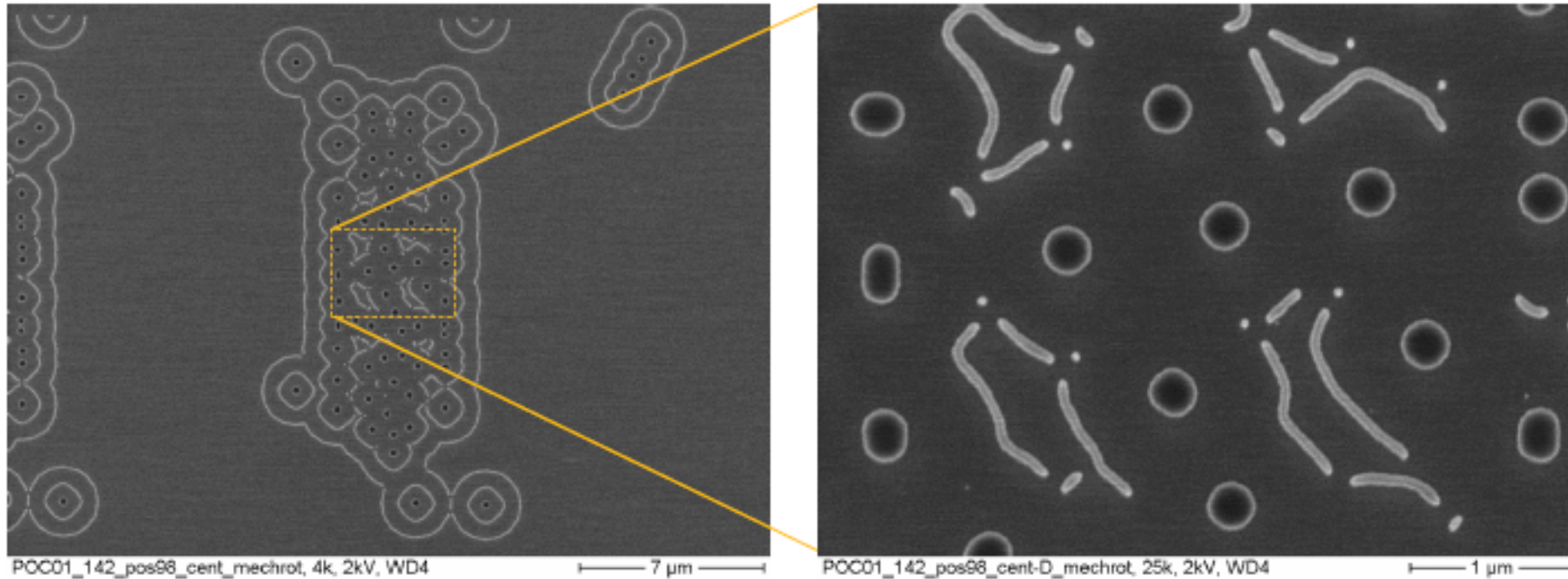
B.G. Kim, et al., BACUS, 2012

ILT Mask Patterns

# Multi-beam is Great for Curvilinear ILT

ILT test pattern design: DNP

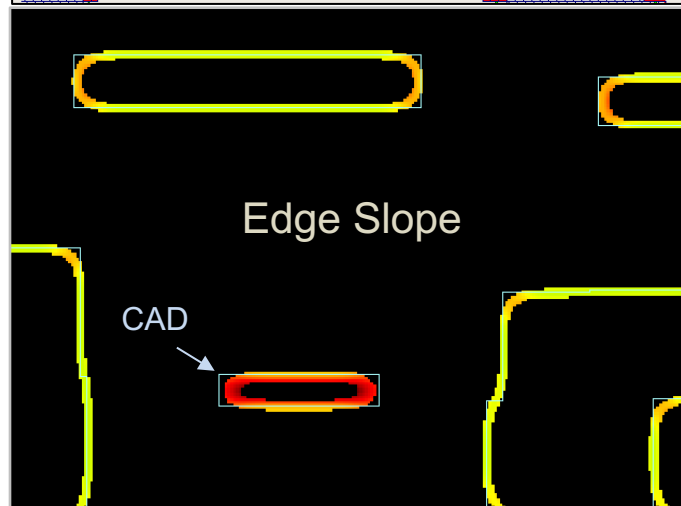
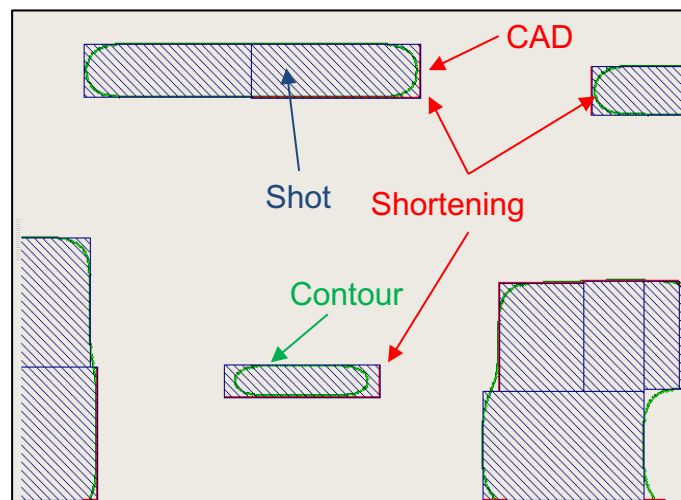
50nm dots, 75nm lines



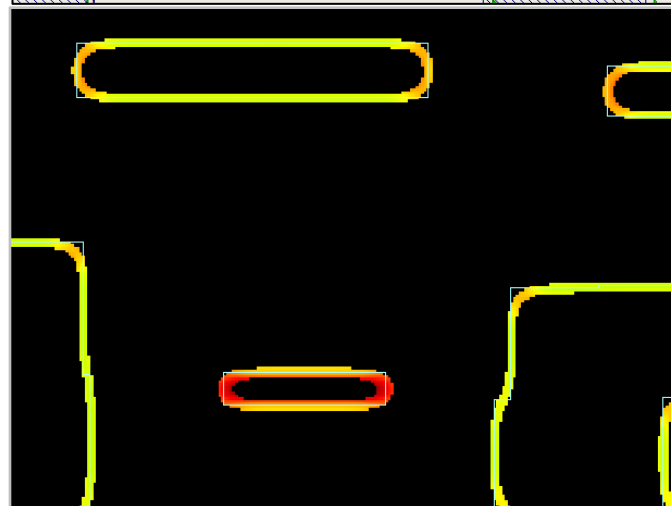
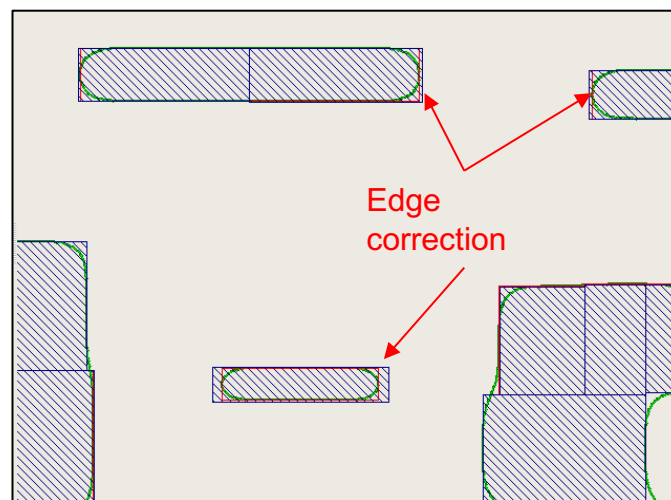
Courtesy of IMS paper: alpha machine

## Multi-beam exposure without loss of TPT

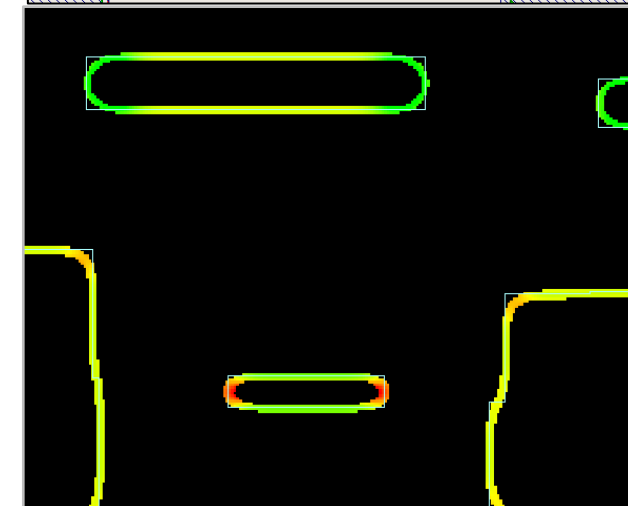
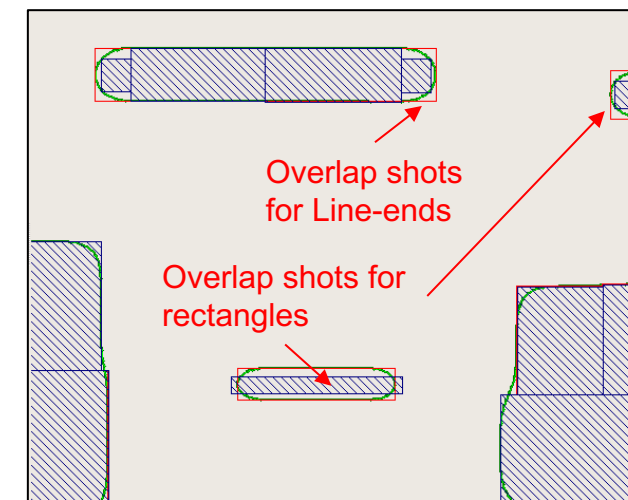
# MPC Needs Dose and Shape Corrections



Without MPC



Shape Correction



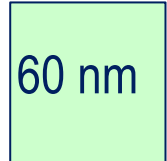
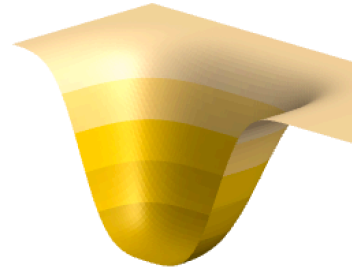
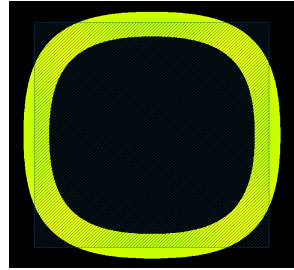
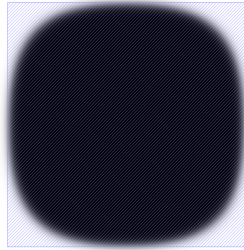
Shape + Dose Correction



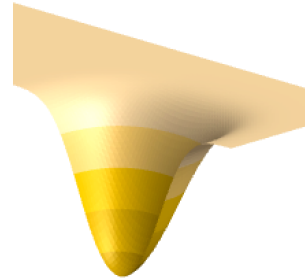
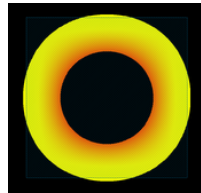
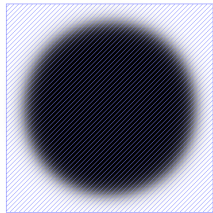
# Curvilinear ILT MPC on VSB: Both Dose and Shape Correction Needed



100 nm

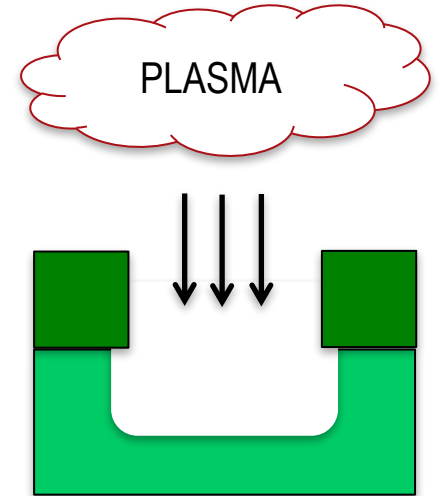


60 nm



Shot Size   Exposed Resist   Edge Slope

Resist Profile



Small feature's resist profile will be bad,  
shape correction won't help

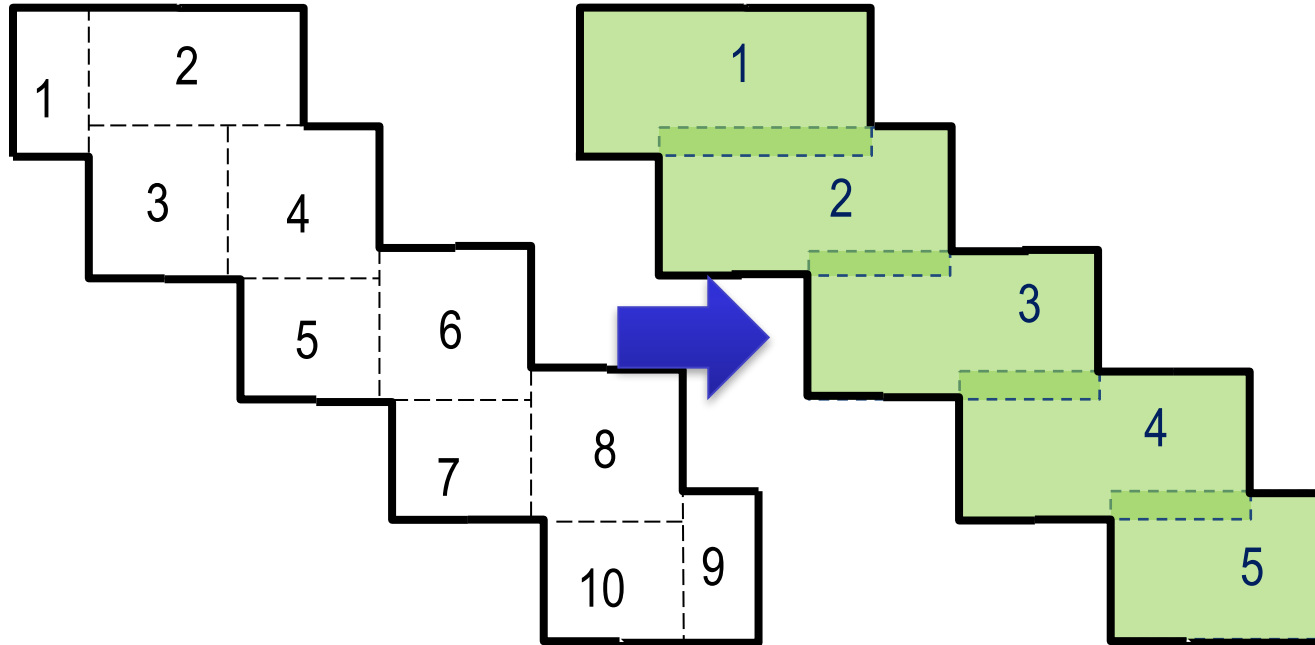
Resist image correction is better to be done by dose correction

Etching and nonlinearity  
better to be corrected by  
shape correction



# Curvilinear ILT MPC on VSB: Overlapping Shots Help

10 conventional shots      5 overlapping shots  
Plus, extra energy in overlapping areas



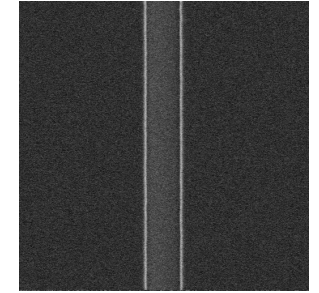
Conventional Shots (2143 shots)



Overlapped Shots (1057 shots)

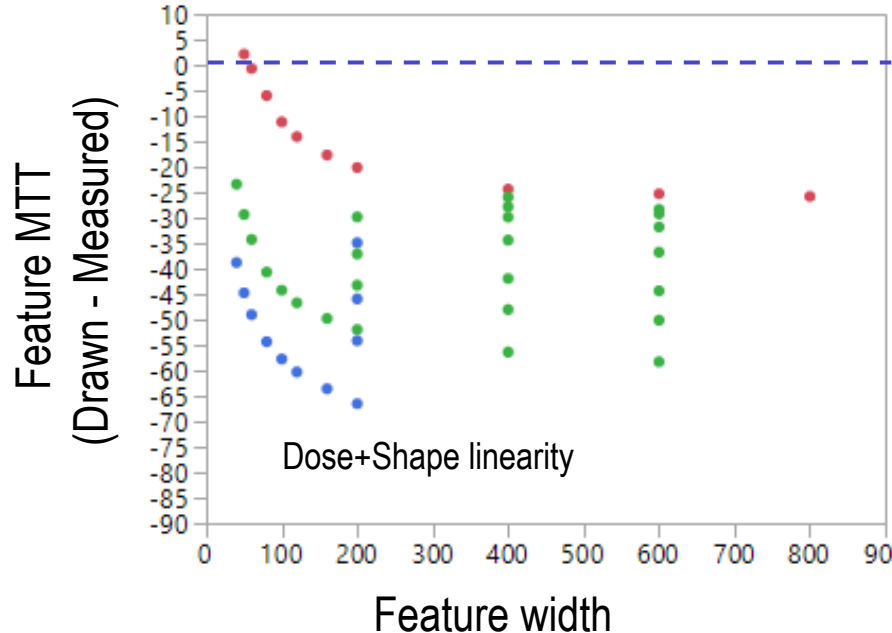
Overlapping shots cast more energy in less write time:  
= Better process margin  
= Better CDU  
= No mask-write time vs. mask-quality compromise

# Curvilinear ILT MPC on VSB: The Mask Model Has to Consider Dose Change



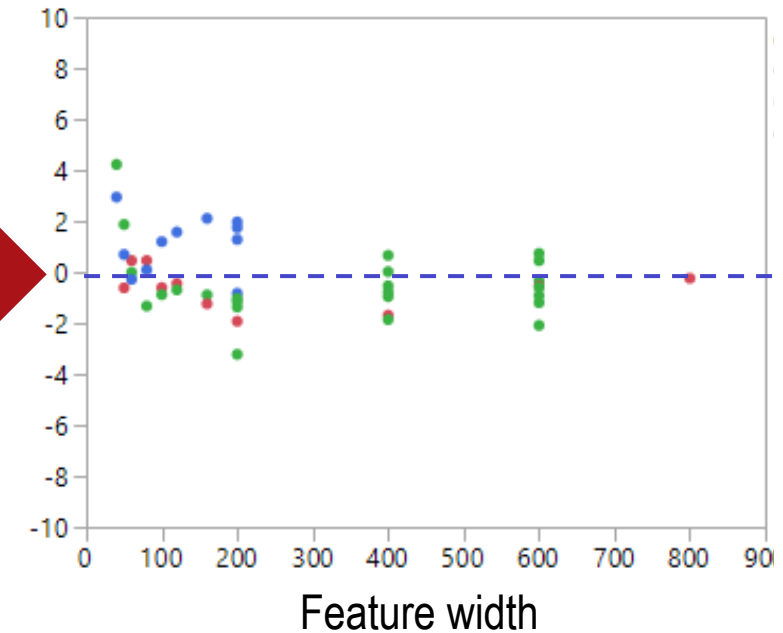
Iso Lines

Non-zero y-axis values mean:  
mask print errors if uncorrected



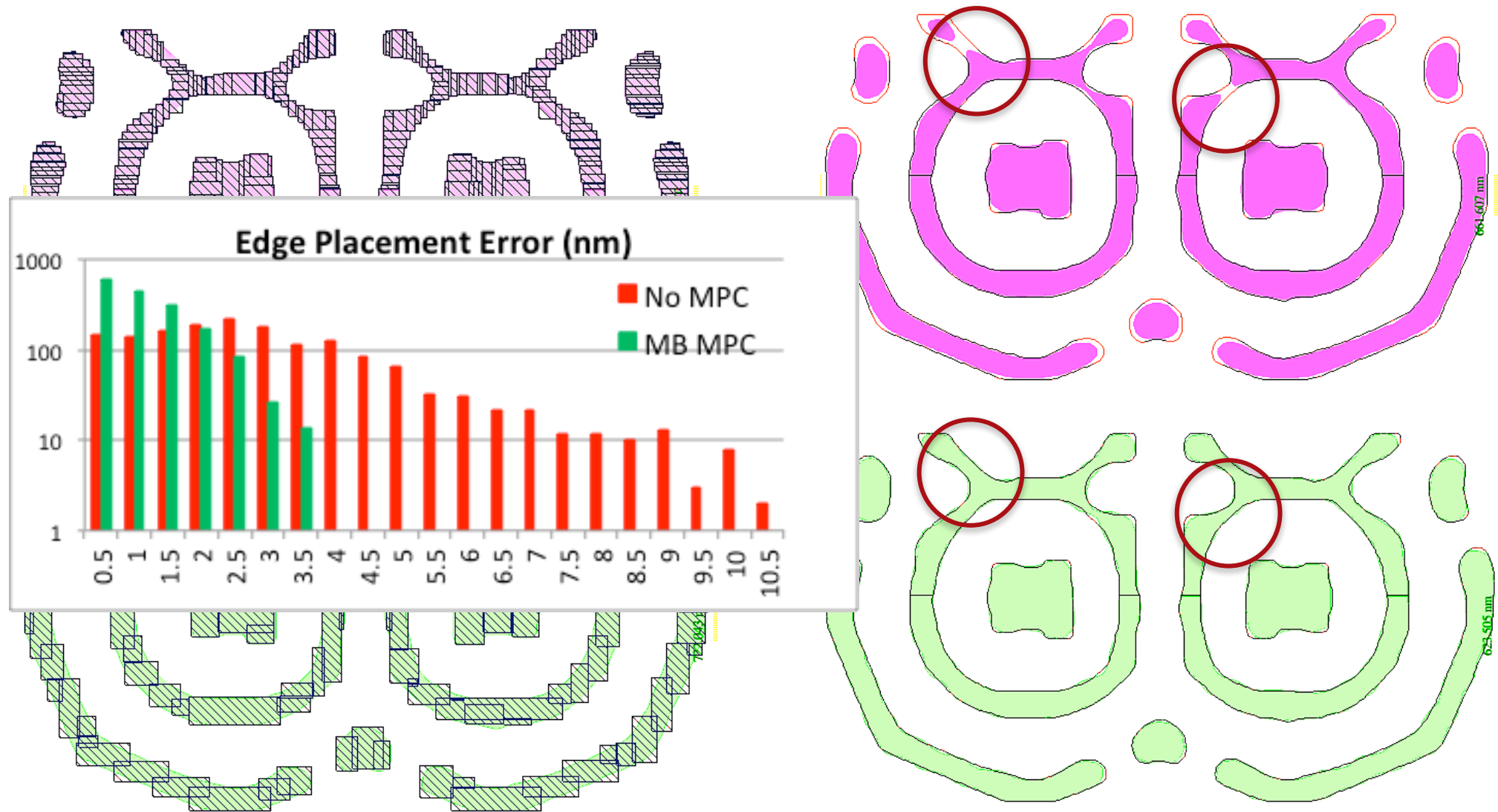
Feature MTT  
(Drawn - Measured)

30nm to 4nm

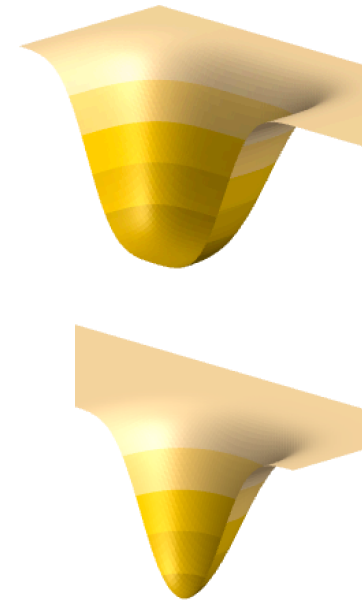
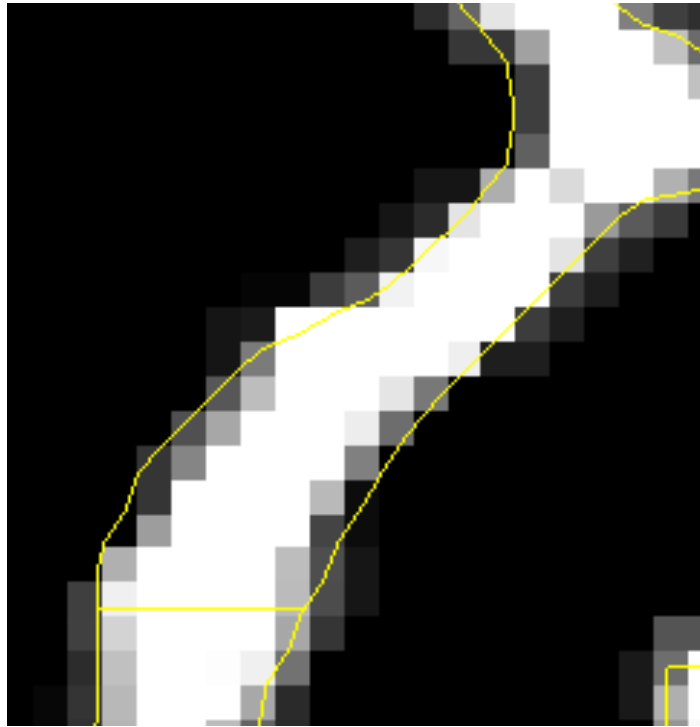


Ref: EUV Modeling in the Multi-Beam mask making Era, Ryan Pearman

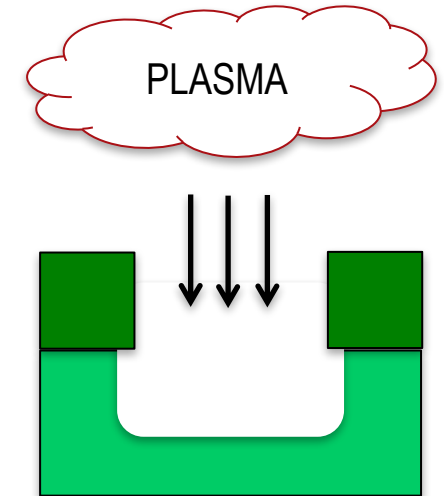
# Curvilinear ILT MPC on VSB: Improving CDU



# Curvilinear ILT MPC on Multi-beam: Both Dose and Shape Correction Needed



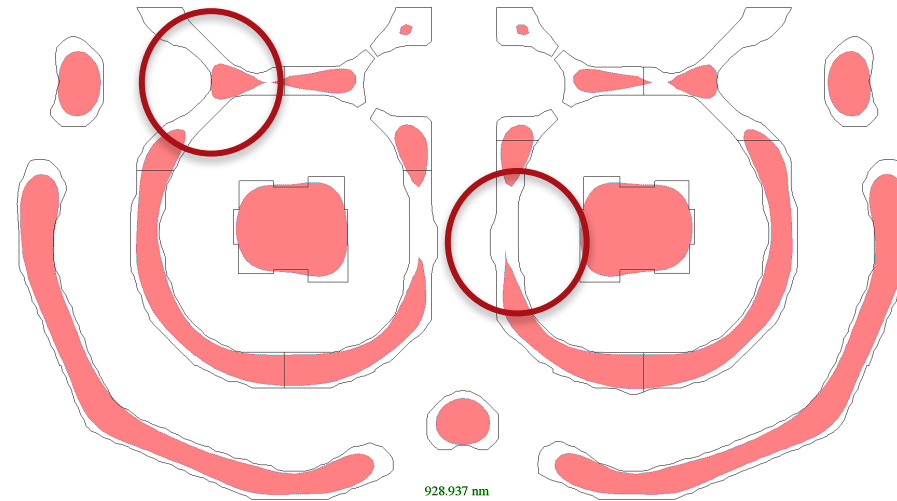
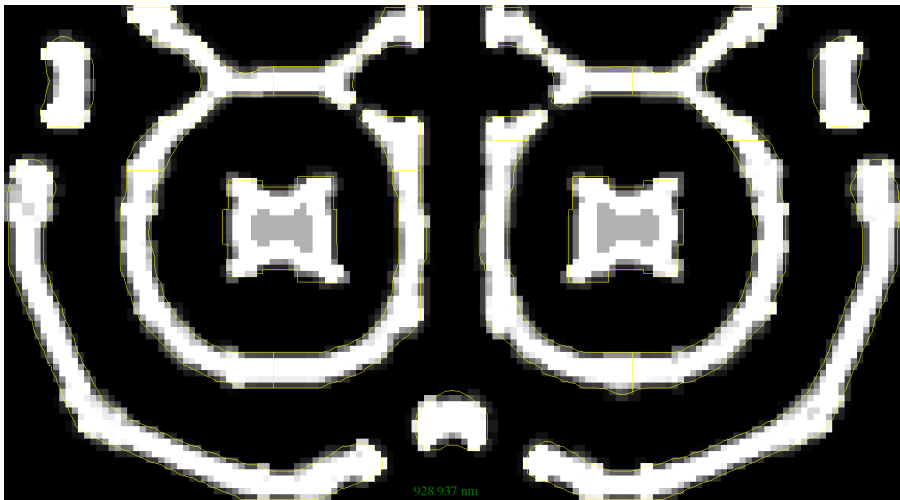
Resist Profile



Dose modulation on each beam pixel is the best  
Resist image correction is better to be done by dose correction

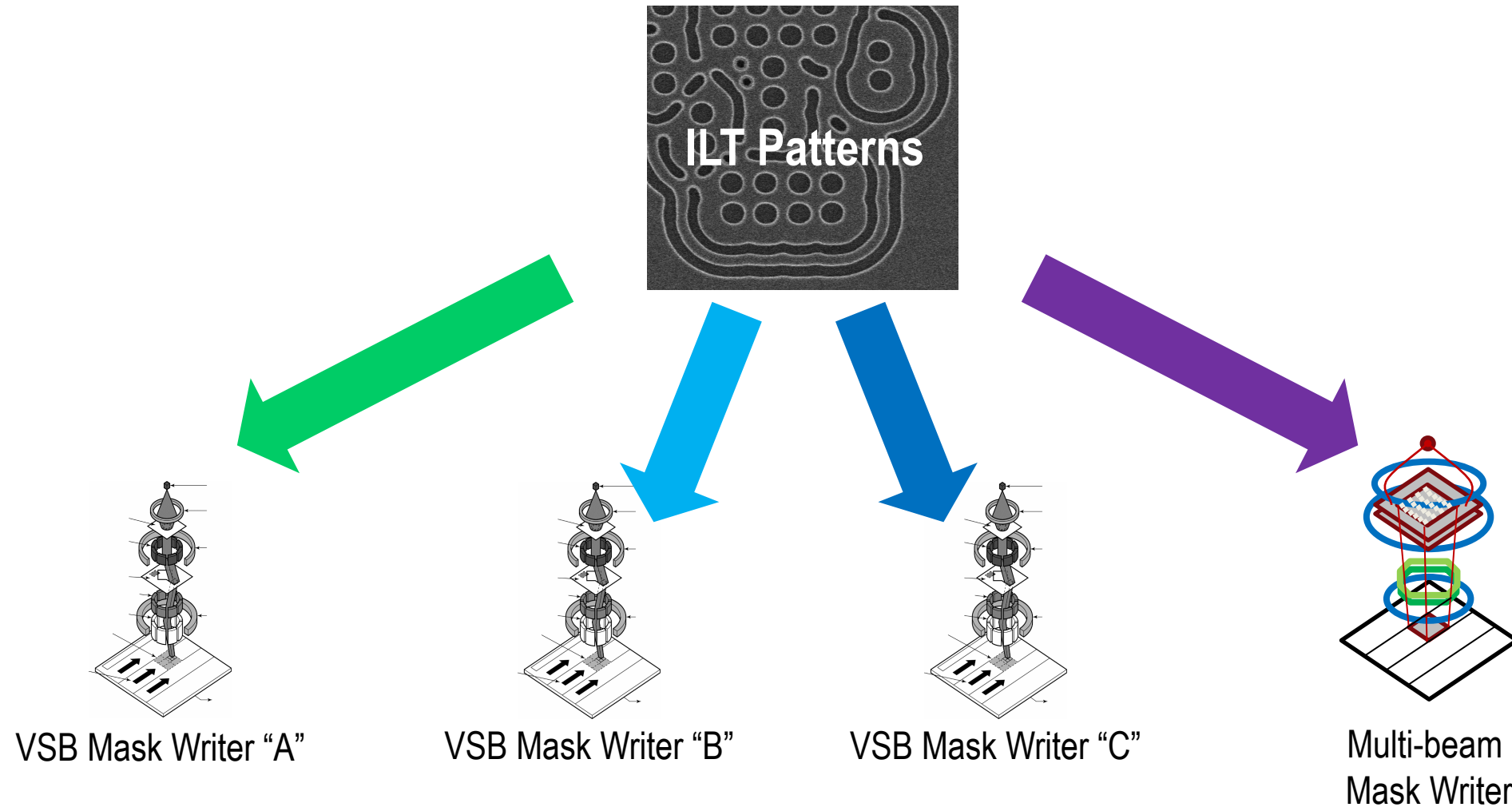
Etching and nonlinearity  
better to be corrected by  
shape correction

# Curvilinear ILT MPC on Multi-beam: Improving CDU



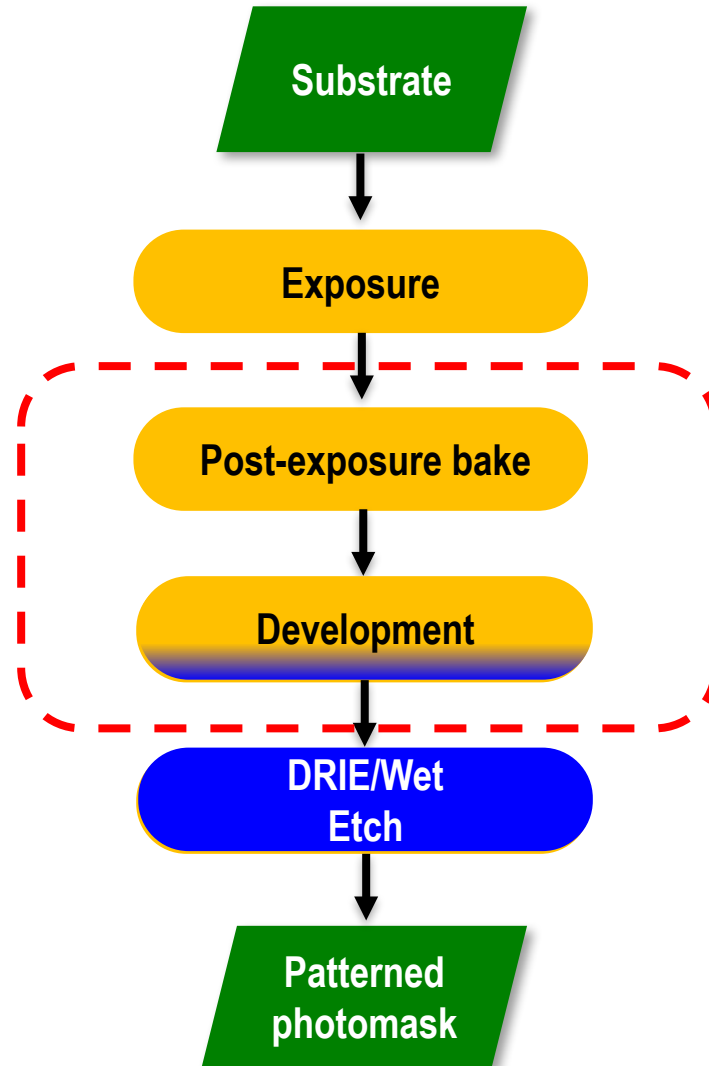
Refer to: GPU-Accelerated Inline Mask Correction  
for the MBM-1000, H. Zable, Aki Fujimura

# To Enable ILT MPC Portability, Model Has to be the Same

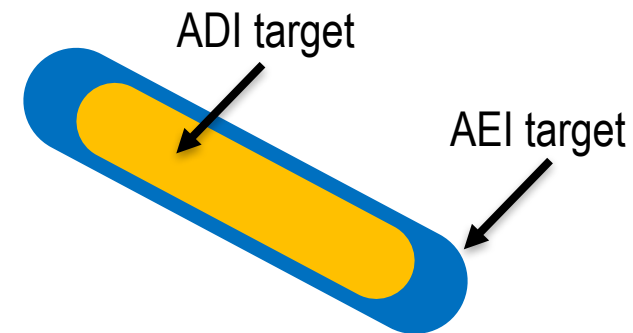
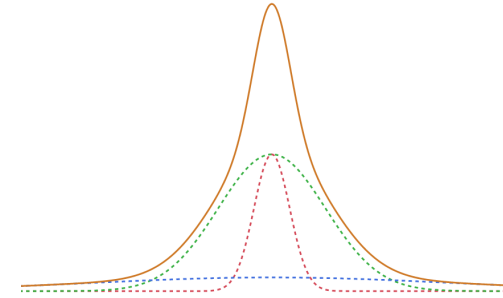




# VSB and Multi-beam Can Share the Same Mask Model

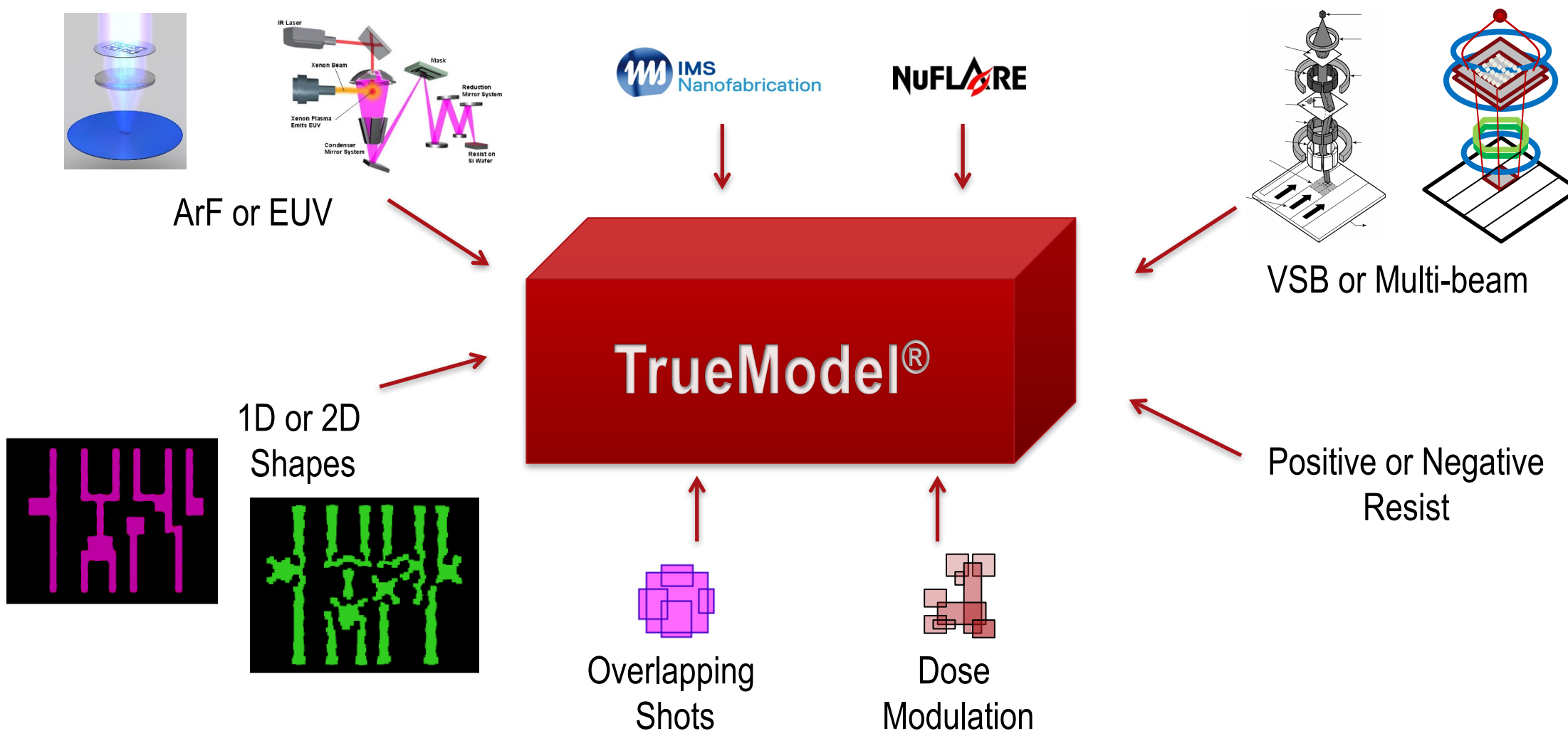


Dose effects



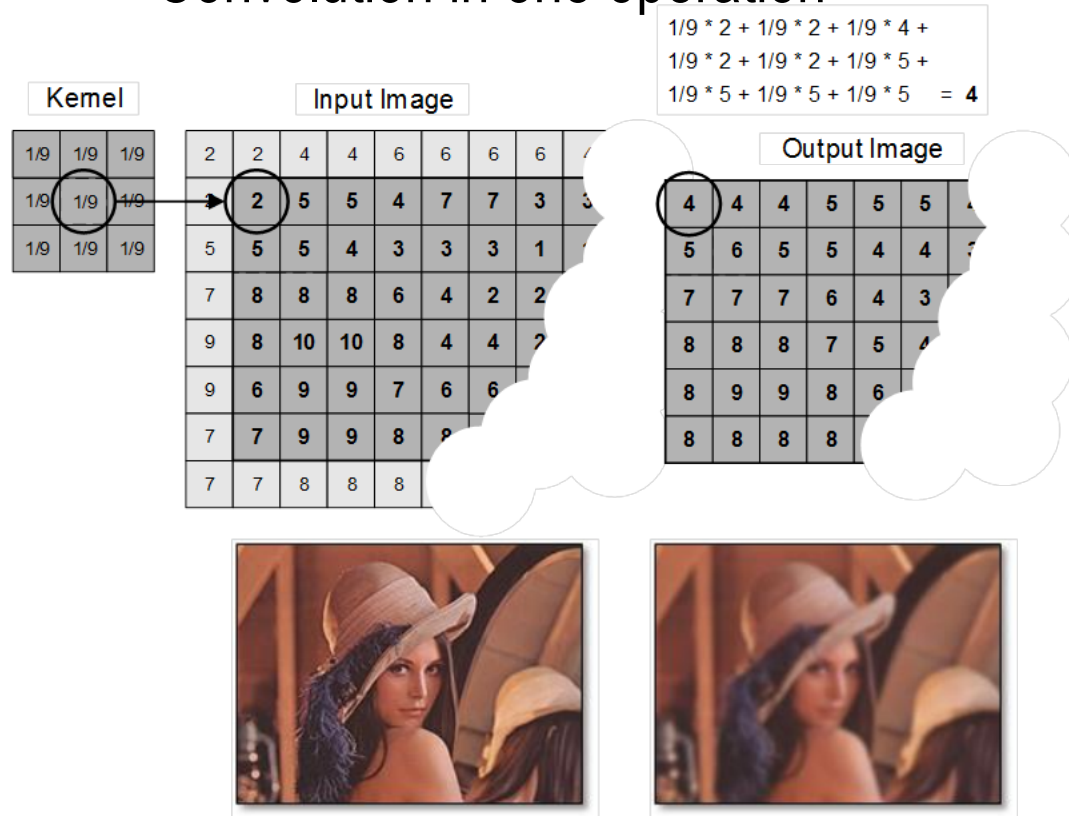
Shape effects

# One Model Form is All You Need for All Masks



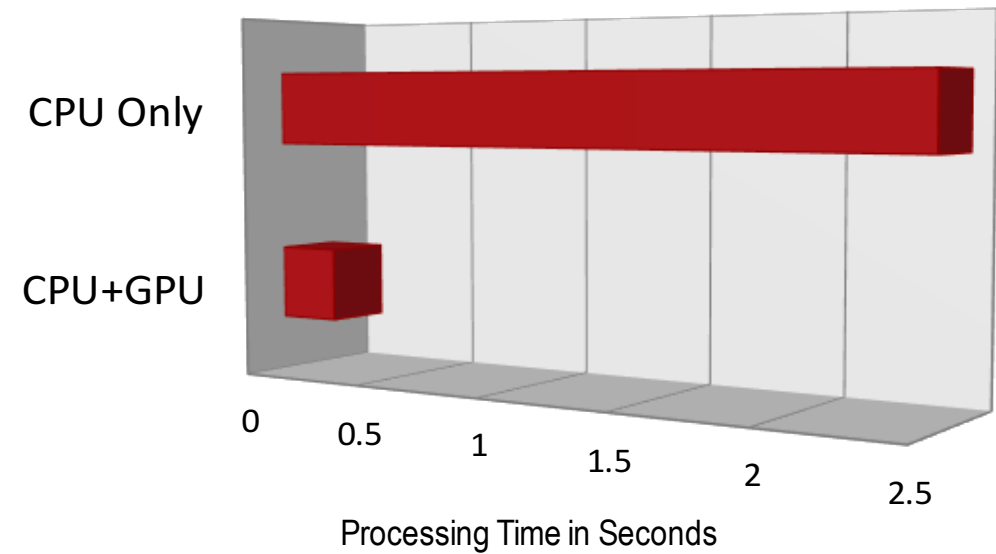
# GPU is Good for Mask Model and Simulation

- GPU is designed to do image processing really fast
  - Convolution in one operation



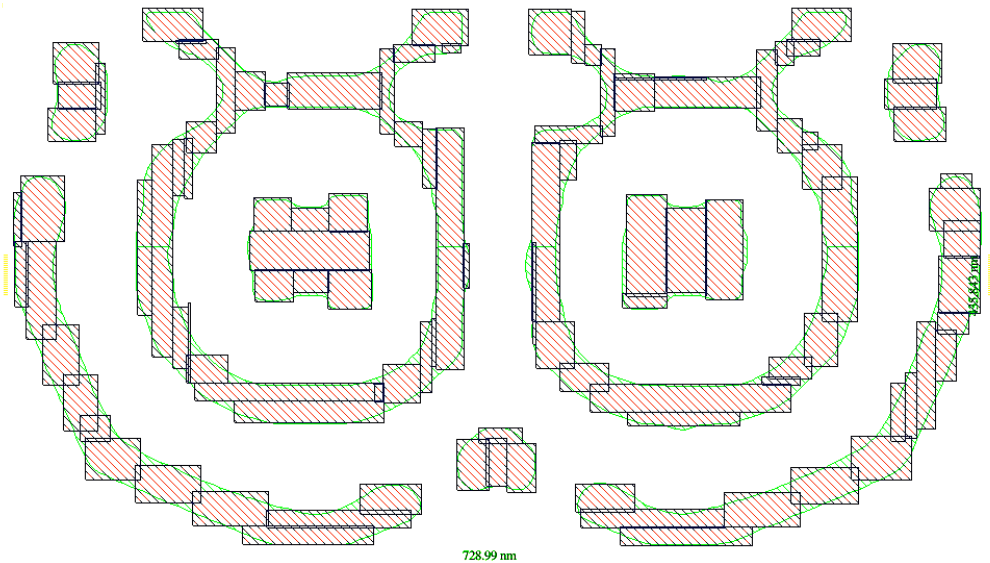
- Thousands of pipeline to massively distribute the run for same operation and multiple data

Gaussian convolution run on CPU-Only and on CPU+GPU  
Data size: ~80  $\mu$ m by 80 $\mu$ m, 10nm pixels

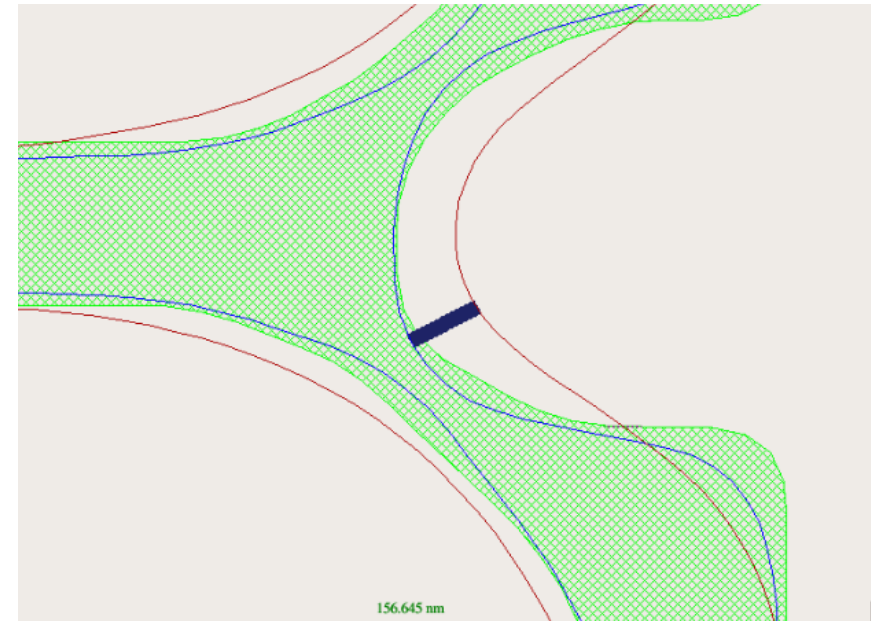


Ref: Heterogeneous compute case study: image convolution filtering, Imagination Blog

# GPU is Good for Both Dose and Shape Correction



GPU is Good for Dose Correction



GPU is Good for All Angle Geometry Engine

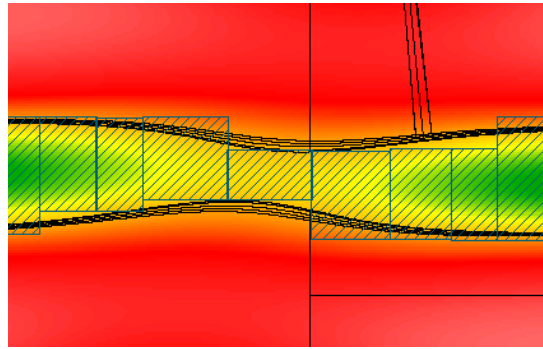
Refer to: Simulation-Based MDP Verification  
for Leading-Edge Masks, Bo Su

# GPU-Accelerated MB-MPC Enables Curvilinear ILT Using Either VSB or Multi-Beam Mask Writer



- Curvilinear ILT requires model-based mask process correction
- Multi-beam mask writer is ideal for curvilinear ILT because of the constant write time
- VSB mask writer needs to write curvilinear ILT as a backup of multi-beam
- Both dose and shape correction are required for MPC on VSB and multi-beam
- A single model can be used for both, enabling ILT portability
- GPU enables model-based MPC with reasonable runtimes
  - Fast physical model computing, dose compensation, and all-angle geometry engine

# My Prediction: GPU Will Become the De Facto Computing Platform for Semiconductor Manufacturing



Simulation

B.G. Kim, et al., BACUS, 2012

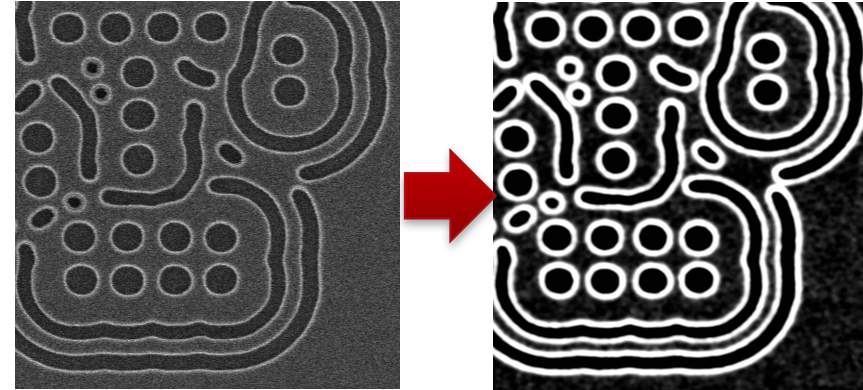
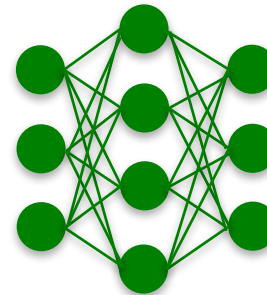


Image Processing



(Deep) Machine learning



